AW313A Datasheet

Zhuhai Jieli Technology Co.,LTD

Version 1.0

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Revision History

Date	Revision	Description
2024.04.12	V1.0	Initial Release





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AW313A Features

SYSTEM

- > 32bit CPU 160MHz
- ➤ Support MATH/AES128
- I-cache
- Support EMU
- On-chip SRAM 32kbyte
- Support MPU
- Support UDMA
- Built-In Flash
- ➤ 24MHz crystal oscillator
- > Internal low jitter low power RC oscillator
- Internal PLL

Bluetooth

- BLE5.4 +2.4GHz-Proprietary (QDID 223418)
- Support AoA Transmitter
- Support long range BLE
- Maximum transmitting power 9dBm
- Receiver sensitivity
 - ❖ -96dBm @BLE-1Mbps
 - ◆ -93dBm @BLE-2Mbps

Peripherals

- 1 x Full speed USB
- 4 x Multi-function 32bit timer
- ➤ 1 x IR RX/TX
- 3 x UART interface
- 1 x I²C Master/Slave interface
- 2 x SPI Master/Slave interface
- ➤ 1 x QDEC
- ➤ 4 x MCPWM
- ➤ 2 x LEDC
- 1 x 10bit ADC(13 Channel)
- ▶ 12 x GPIO Support function remapping

PMU

- Support temperature sensor
- ➤ VPWR range 2.7V to 5.5V
- ➤ IOVDD range 1.8V to 3.6V
- > Deep sleep mode (IOVDD @3.0V)
 - 170nA (External wakeup)
 - 1.37uA (32kHz RC OSC+wakeup)
 - 2.9uA (32kHz RC OSC+wakeup+16k retention SRAM)

Packages

QFN20(3mm*3mm)

Temperature

- Operating temperature
 - TC = -20° C to $+85^{\circ}$ C(standard range)
 - $TC = -40^{\circ}C$ to $+105^{\circ}C$ (extended range)
- Storage temperature -65°C to +150°C

Applications

- Mouse devices
- Non-audio remote controller
- Selfie stick
- Page turner
- Adaptive USB
- Bluetooth moudle
- Price tag and other diversified IOT product



1 Block Diagram

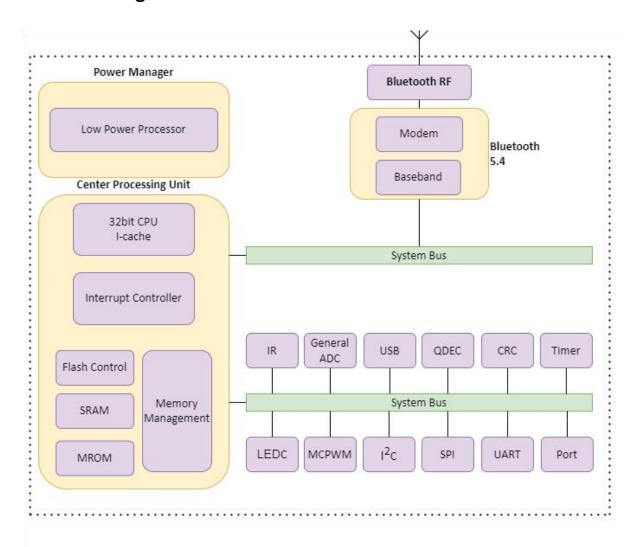


Figure 1-1 AW313A Block Diagram



2 Pin Definition

2.1 Pin Assignment

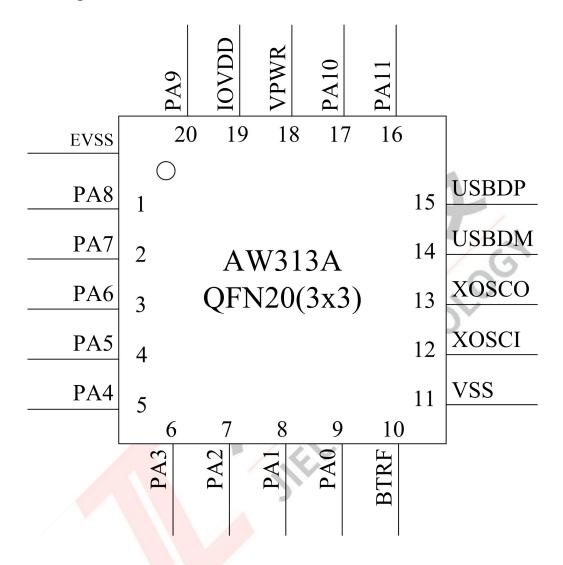


Figure 2-1 AW313A Pin Assignment



2.2 Pin Description

Table 2-2-1 AW313A Pin Description

Pin No.	Name	Туре	IO Initial	Description
1 111 140.	Hume	Type	State	Description
1	PA8	1/0	Z	ADC8(ADC Input Channel 8)
_	FAO	1,0		SPIO_DAT2B
2	PA7	1/0	Z	
3	PA6	1/0	Z	ADC6(ADC Input Channel 6)
4	PA5	1/0	Z	ADC5(ADC Input Channel 5)
5	PA4	1/0	10kΩ Pull-up	ADC4(ADC Input Channel 4)
3	PA4	170	10Kt2 Pull-up	MCLR(Device Reset)
6	PA3	1/0	Z	ADC3(ADC Input Channel 3)
0	PAS	170		SPIO_DIB(1)
7	PA2	1/0	Z	ADC2(ADC Input Channel 2)
,	PAZ	170		SPIO_DOB(0)
8	PA1	1/0	Z	ADC1(ADC Input Channel 1)
٥	PAI	170		SPIO_CLKB
9	PA0	1/0	Z	ADC0(ADC Input Channel 0)
10	BTRF	RF		Bluetooth RF Antenna
11	VSS	G	/> /	Ground
12	XOSCI	1		Crystal Oscillator Input
13	xosco	0		Crystal Oscillator Output
14	USBDM	1/0	15kΩ Pull-down	ADC13(ADC Input Channel 13)
15	USBDP	1/0	15kΩ Pull-down	ADC14(ADC Input Channel 14)
16	PA11	1/0	10kΩ Pull-up	ADC11(ADC Input Channel 11)
10	PAII	1/0	10K12 Pull-up	Hold down 0 to reset
17	PA10	1/0	Z	ADC10(ADC Input Channel 10)
18	VPWR	Р		Battery Input
19	IOVDD	Р		IO Power
		_		LVD(External Low Voltage Detection Input)
20	PA9	1/0	z	ADC9(ADC Input Channel 9)
				SPIO_DAT3B

Note

1.IO initial state abbreviations Z--High resistance, H--High level, L--Low level, X--May be changed during power on.

2.Timer, IR,MCPWM, QDEC, UART, LEDC, I²C, SPI1 functions can be remapped to any I/O.

Table 2-2-2 Pin Types Description

Pin Type	Description	Pin Type	Description
Р	Power	I/O	Input or Output
G	Ground	I	Input

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Pin Type	Description	Pin Type	Description
RF	RF antenna	0	Output





3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1 Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
Topt	Operating temperature	-20	+85	$^{\circ}$
Tstg	Storage temperature	-65	+150	$^{\circ}$
VPWR	Consta Valle co	-0.3	6.0	V
IOVDD	Supply Voltage	-0.3	3.6	V
GPIO	Input voltage of GPIO (except PA7)	-0.3	3.6	V
HVTIO	Input voltage of HVT-IO (PA7)	-0.3	6.0	V

Note

3.2 ESD Ratings

Table 3-2 ESD Ratings

Parameter	Тур	Test pin	Reference standard
Human Body Mode	±8kV	All pins	JEDEC EIA/JESD22-A114
Machine Mode	±400V	All pins	JEDEC EIA/JESD22-A115
Charge Device Model	±2kV	All pins	ANSI/ESDA/JEDEC JS-002-2022

3.3 PMU Characteristics

Table 3-3-1 PMU Characteristics under VPWR supply

	The state of the s						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
VPWR	Power supply	-	2.7		5.5	V	
Operating mo	Operating mode						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
IOVDD	Voltage output			3.0		V	
טטעטו	Loading current	IOVDD=3.0V@VPWR = 3.7V			60	mA	
Low Power me	ode						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
IOVDD	Loading current	IOVDD=3.0V@VPWR = 3.7V			8	mA	

Table 3-3-2 PMU Characteristics under IOVDD supply

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
IOVDD	Power supply	-	1.8		3.6	V

^{1.}Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device.



3.4 IO Characteristics

Table 3-4 IO Characteristics

Input Chai	racteristics					
Symbol	Parameter	Conditions	10	Min	Max	Unit
V _{IL}	Low-Level Input Voltage	IOVDD = 3.0V	PAO~PA11	-0.3	1.4	V
			PA0~PA6			
			PA8~PA11			
V_{IH}	High-Level Input Voltage	IOVDD = 3.0V	USBDP	1.7	3.3	V
			USBDM			
		IOVDD = 3.0V	PA7	1.7	5.5	V
Output Ch	aracteristics					
Symbol	Parameter	Conditions	10	Ty	/p	Unit
				3(H	D=0)	
		IOVDD = 3.0V	PA0~PA6	9(H	D=1)	
		Voutput = 0.3V	PA8~PA11	21(H	D=2)	mA
I _{OL}	Output Current		76/	54(HD=3		
			PA7			
			IOVDD = 3.0V USBDP		8	
		Voutput = 0.3V	USBDM			
				3(HD=0) 9(HD=1) 21(HD=2) 54(HD=3)		mA
		IOVDD = 3.0V	PA0~PA6			
		Voutput = 2.7V	PA8~PA11			
I _{OH}	Output Current					
		10,100 3,01	PA7			
		IOVDD = 3.0V USBDP		8		mA
		Voutput = 2.7V	USBDM			
Internal R	esistance Characteristics					
Symbol	Parameter	Conditions	10	Ty	ур	Unit
				10k(F	PU=1)	
		IOVDD = 3.0V	PAO~PA11	100k(PU=2)	Ω
R_{pu}	Pull-up Resistance			1M(F	PU=3)	
		IOVDD = 3.0V	USBDP	1.	5k	Ω
		IOVDD = 3.0V	USBDM	18	0k	Ω
				10k(I	PD=1)	
		IOVDD = 3.0V	PA0~PA11	100k(PD=2)	Ω
R_{pd}	Pull-down Resistance			1M(PD=3)		
		IOVDD = 3.0V	USBDP	15k		Ω
		1 10VDD = 3 OV	İ			

Note

1.Internal pull-up/pull-down resistance accuracy ±20%.



3.5 BT Characteristics

3.5.1 Transmitter

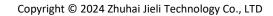
Table 3-5-1 Transmitter characteristics

Parameter	Conditions	Min	Тур	Max	Unit
Maximum RF Transmit Power	BLE-1Mbps		8	9	dBm

3.5.2 Receiver

Table 3-5-2 Receiver characteristics

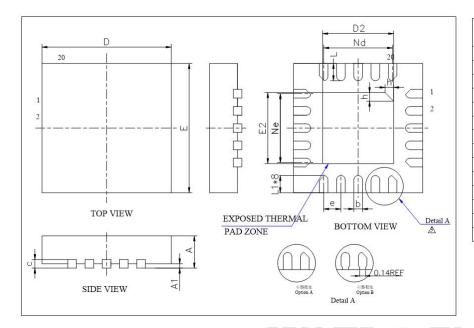
Parameter	Conditions	Min	Тур	Max	Unit
	BLE-1Mbps		-96		dBm
	BLE-2Mbps	/	-93		dBm
Sensitivity	BLE-S2	\	-99		dBm
	BLE-S8	-	-103.5	//	dBm





4 Package Information

4.1 QFN20_3×3mm



SYMBOL	MILLIMETER			
	MIN	NOM	MAX	
A	0.70	0.75	0.80	
A1	344	0.02	0.05	
ь	0.15	0.20	0.25	
С	0.18	0.20	0.25	
D	2.90	3.00	3.10	
D2	1.40	1.60	1.80	
e	0.40BSC			
Ne	1.60BSC			
Nd	1.60BSC			
E	2.90	3.00	3.10	
E2	1.40	1.60	1.80	
L	0.35	0.40	0.45	
L1	0.30	0.40	0.50	
h	0.20	0.25	0.30	

Figure 4-1 AW313A Package



5 IC Marking Information

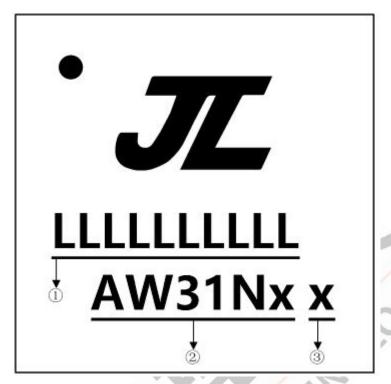


Figure 5-1 AW313A Package Outline

- 1 LLLLLLLL Production Batch
- 2 AW31Nx Chip Model
- 3 x Built-in flash size
 - 0 No Flash Memory
 - 2 2Mbit Flash
 - 4 4Mbit Flash



6 Solder-Reflow Condition

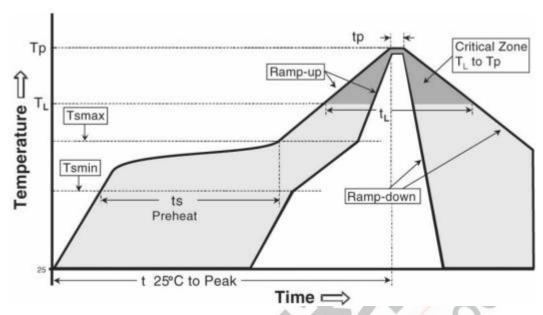


Figure 6-1 Classification Reflow Profile

Table 6-1 Classification Profiles

	Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly	
	Temperature Min (T _{smin})	100℃	150℃	
Preheat/Soak	Temperature Max (T _{smax})	150°C	200℃	
	Time (ts) from (T _{smin} to T _{smax})	60-120 seconds	60-180 seconds	
Average ramp-up rate (T _{smax} to T _p)		3℃/second max	3℃/second max	
Liquidus temperature (T _L)		183℃	217℃	
Time (t _L) maintained <mark>above T_L</mark>		60-150 seconds	60-150 seconds	
Peak package body temperature (T _p)		See Table 6-2	See Table 6-3	
Time within 5℃ of actual		10-30 seconds	20-40 seconds	
Peak Temperat	cure (tp) ²	10-30 Seconds	20-40 Seconds	
Ramp-down rate (Tp to TL)		6°C/second max	6℃/second max	
Time 25℃ to peak temperature		6 minutes max	8 minutes max	

Note

- 1.All temperatures refer to topside of the package, measured on the package body surface
- 2.Time within 5 $^{\circ}$ C of actual peak temperature (tp) specified for the reflow profiles is a "supplier" and "user" maximum.

Table 6-2 SnPb Classification Temperature

Package	Volume mm ³	Volume mm³ ≥ 350	
Thickness	< 350		
<2.5 mm	240 +0/-5℃	225 +0/-5°C	
≥2.5 mm	225 +0/-5℃	225 +0/-5°C	



Table 6-3 Pb-free - Classification Temperature

	·		
Package	Volume mm³	Volume mm³	Volume mm³
Thickness	< 350	350 - 2000	> 2000
< 1.6mm	260℃	260℃	260 ℃
1.6 mm - 2.5mm	260℃	250℃	245℃
> 2.5mm	250℃	245℃	245℃

Note

1.*Tolerance The device manufacturer/supplier shall assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0 $^{\circ}$ C.For example 260 $^{\circ}$ C+0 $^{\circ}$ C)at the rated MSL level.

